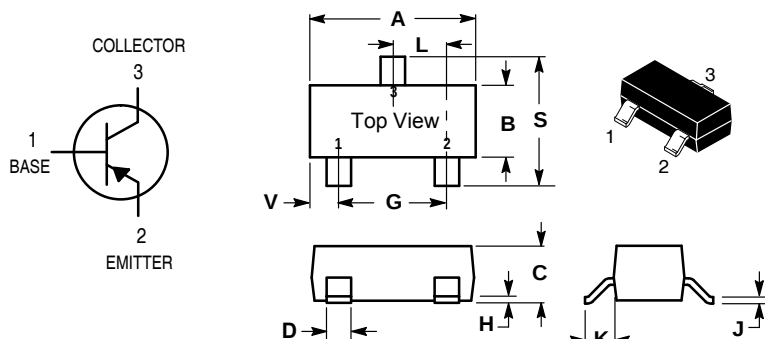


RoHS Compliant Product

FEATURES

A suffix of "-C" specifies halogen & lead-free

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT2222A)
- Ideal for Medium Power Amplification and Switching



MAXIMUM RATINGS

Rating	Symbol	2907	2907A	Unit
Collector–Emitter Voltage	V_{CEO}	–40	–60	Vdc
Collector–Base Voltage	V_{CBO}	–60		Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current — Continuous	I_C	–600		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board ⁽¹⁾ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, ⁽²⁾ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

SOT-23		
Dim	Min	Max
A	2.800	3.040
B	1.200	1.400
C	0.890	1.110
D	0.370	0.500
G	1.780	2.040
H	0.013	0.100
J	0.085	0.177
K	0.450	0.600
L	0.890	1.020
S	2.100	2.500
V	0.450	0.600
All Dimension in mm		

DEVICE MARKING

MMBT2907 = M2B; MMBT2907A = 2F

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽³⁾ ($I_C = -10\text{ mAdc}$, $I_B = 0$)	MMBT2907 MMBT2907A	$V_{(BR)CEO}$	–40 –60	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{Adc}$, $I_E = 0$)		$V_{(BR)CBO}$	–60	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{Adc}$, $I_C = 0$)		$V_{(BR)EBO}$	–5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = -30\text{ Vdc}$, $V_{BE(off)} = -0.5\text{ Vdc}$)		I_{CEX}	—	–50	nAdc
Collector Cutoff Current ($V_{CB} = -50\text{ Vdc}$, $I_E = 0$)	MMBT2907 MMBT2907A	I_{CBO}	— —	–0.020 –0.010	μAdc
($V_{CB} = -50\text{ Vdc}$, $I_E = 0$, $T_A = 125^\circ\text{C}$)	MMBT2907 MMBT2907A		— —	–20 –10	
Base Current ($V_{CE} = -30\text{ Vdc}$, $V_{EB(off)} = -0.5\text{ Vdc}$)		I_B	—	–50	nAdc

1. FR–5 = $1.0 \times 0.75 \times 0.062\text{ in.}$

2. Alumina = $0.4 \times 0.3 \times 0.024\text{ in.}$ 99.5% alumina.

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

REM : Thermal Clad is a trademark of the Bergquist Company.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = -0.1\text{ mA}$, $V_{CE} = -10\text{ Vdc}$)	h_{FE}	35	—	—
		75	—	
($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ Vdc}$)		50	—	
		100	—	
($I_C = -10\text{ mA}$, $V_{CE} = -10\text{ Vdc}$)		75	—	
		100	—	
($I_C = -150\text{ mA}$, $V_{CE} = -10\text{ Vdc}$) (3)		—	—	
		100	300	
($I_C = -500\text{ mA}$, $V_{CE} = -10\text{ Vdc}$) (3)		30	—	
		50	—	
Collector-Emitter Saturation Voltage (3) ($I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$) ($I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$)	$V_{CE(sat)}$	—	-0.4 -1.6	Vdc
Base-Emitter Saturation Voltage (3) ($I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$) ($I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$)	$V_{BE(sat)}$	—	-1.3 -2.6	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (3),(4) ($I_C = -50\text{ mA}$, $V_{CE} = -20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	200	—	MHz
Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{EB} = -2.0\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time	$(V_{CC} = -30\text{ Vdc}$, $I_C = -150\text{ mA}$, $I_{B1} = -15\text{ mA}$)	t_{on}	—	45	ns
Delay Time		t_d	—	10	
Rise Time		t_r	—	40	
Turn-Off Time	$(V_{CC} = -6.0\text{ Vdc}$, $I_C = -150\text{ mA}$, $I_{B1} = I_{B2} = -15\text{ mA}$)	t_{off}	—	100	ns
Storage Time		t_s	—	80	
Fall Time		t_f	—	30	

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.
4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

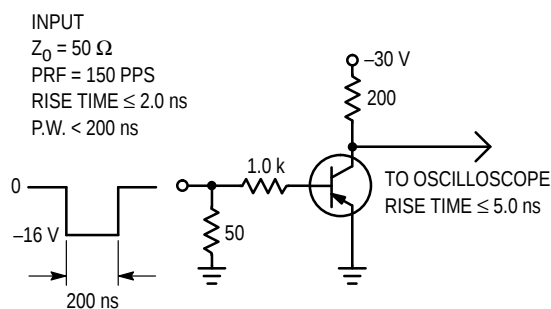


Figure 1. Delay and Rise Time Test Circuit

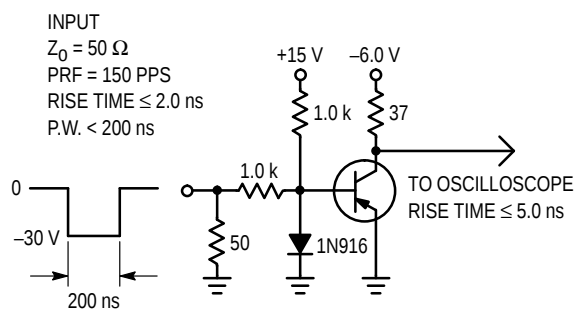


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

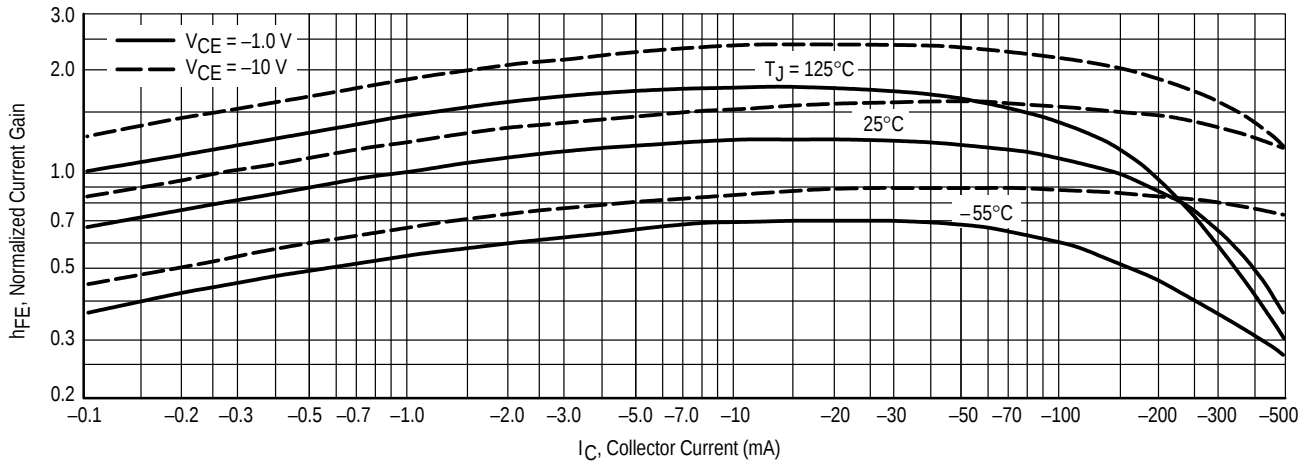


Figure 3. DC Current Gain

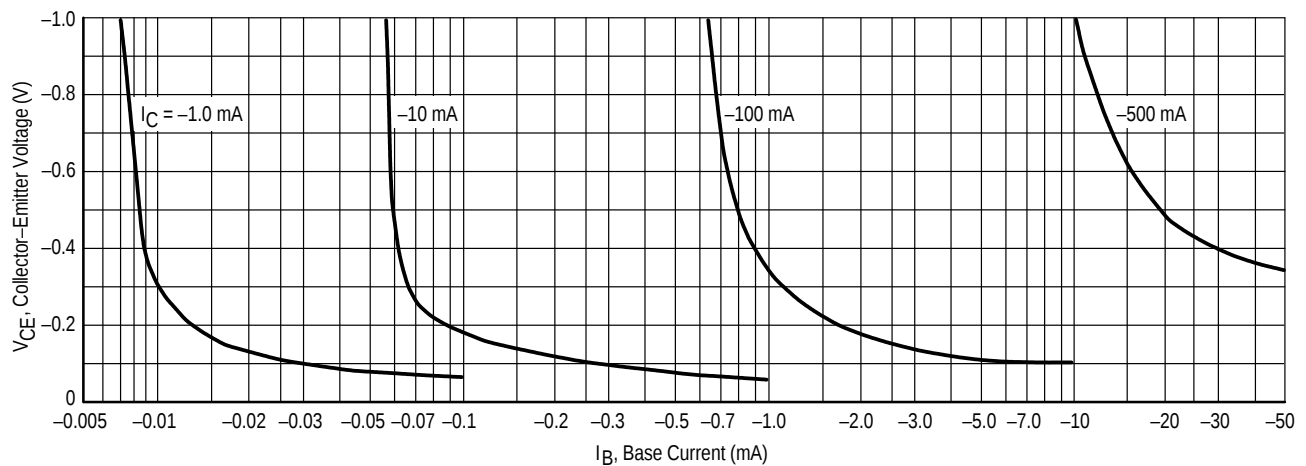


Figure 4. Collector Saturation Region

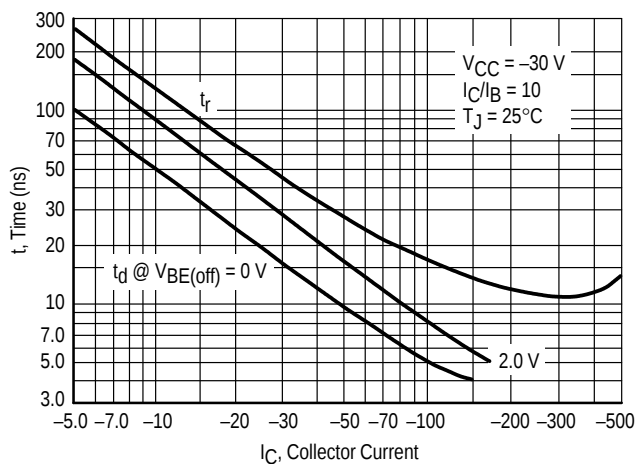


Figure 5. Turn-On Time

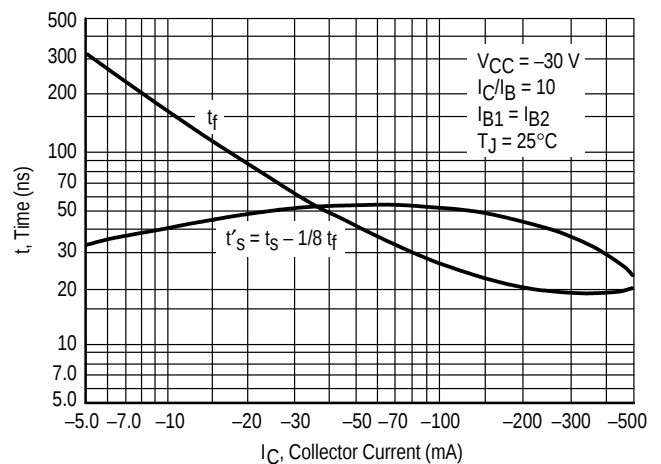


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

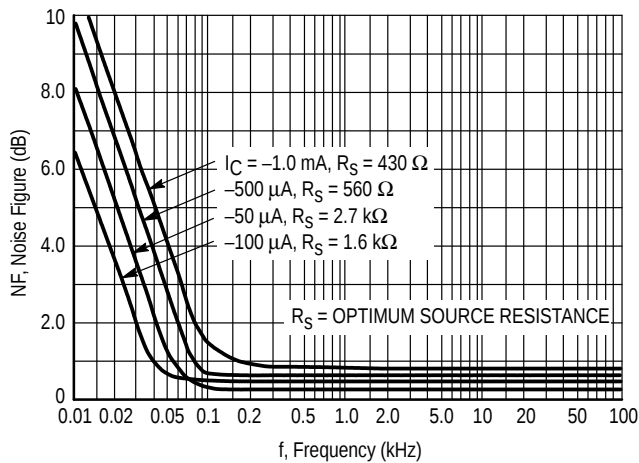


Figure 7. Frequency Effects

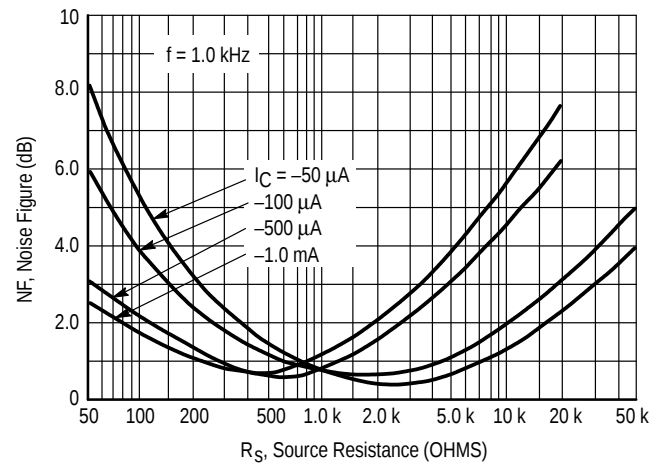


Figure 8. Source Resistance Effects

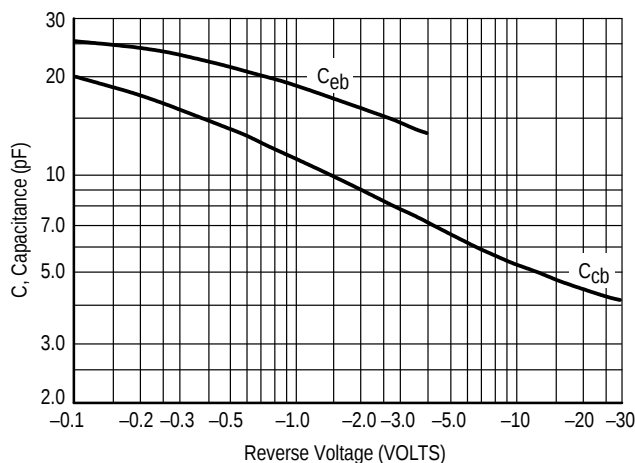


Figure 9. Capacitances

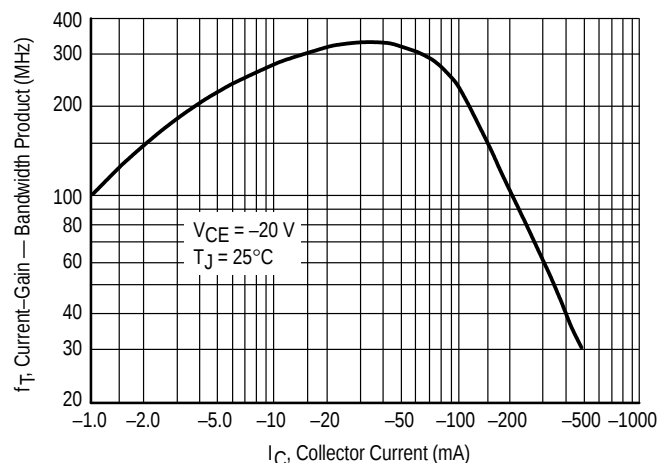


Figure 10. Current-Gain — Bandwidth Product

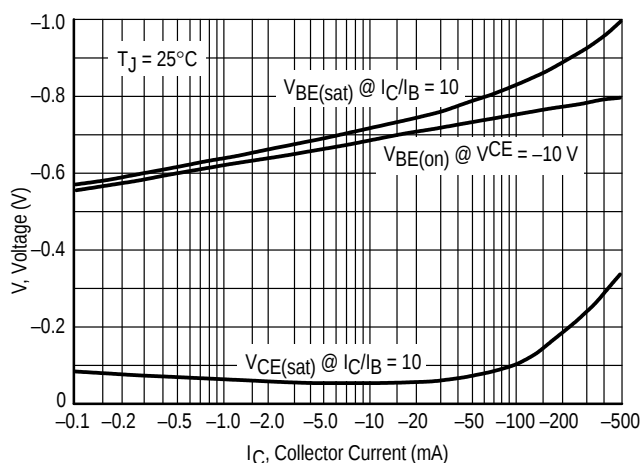


Figure 11. "On" Voltage

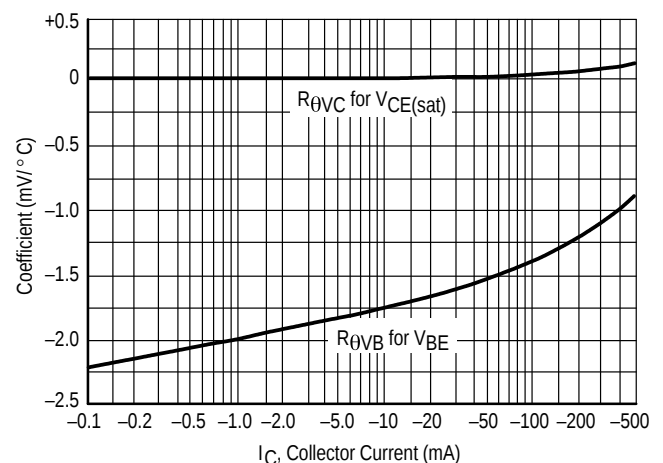


Figure 12. Temperature Coefficients